

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT4S07

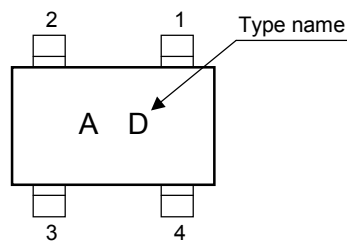
VHF~UHF Band Low Noise Amplifier Applications

- Low Noise Figure: $NF = 1.5\text{dB}$
($V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$, $f = 2\text{ GHz}$)
- High Gain: $|S_{21e}|^2 = 9.5\text{dB}$
($V_{CE} = 3\text{ V}$, $I_C = 15\text{ mA}$, $f = 2\text{ GHz}$)

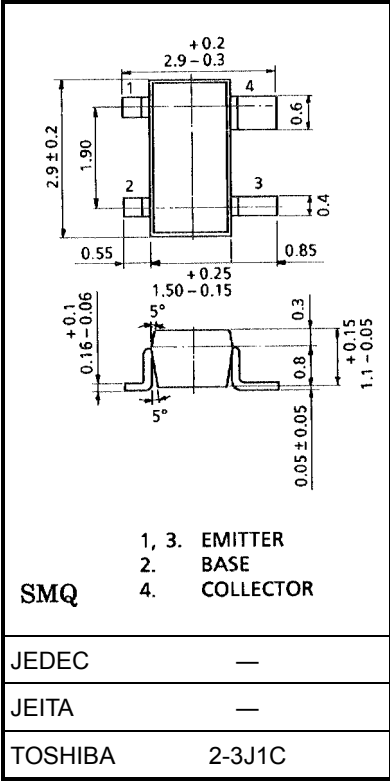
Maximum Ratings (Ta = 25°C)

項 目	記 号	定 格	単位
Collector-base voltage	V_{CBO}	10	V
Collector-emitter voltage	V_{CEO}	5	V
Emitter-base voltage	V_{EBO}	1.5	V
Collector current	I_C	25	mA
Base current	I_B	10	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

Marking



Unit: mm



Weight: 0.012 g (typ.)

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$	10	12	—	GHz
Insertion gain	$ S_{21e} ^2(1)$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	8	—	dB
	$ S_{21e} ^2(2)$	$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}, f = 2 \text{ GHz}$	7.5	10.5	—	
Noise figure	NF(1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	1.6	3	dB
	NF(2)	$V_{CE} = 3 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	1.5	3	

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5 \text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1 \text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$	70	—	140	—
Reverse transfer capacitance	C_{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note)	—	0.4	0.85	pF

Note: C_{re} is measured by 3 terminal method with capacitance bridge.

Caution

This device electrostatic sensitivity. Please handle with caution

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